

WHAT IS CLAIMED IS:

1                   1.       A method for transferring data in a data processing unit comprising:  
2                   receiving a first address;  
3                   if the first address contains a predetermined address component, then  
4                   producing a second address and accessing a memory location at the second address; and  
5                   if the first address does not contain the predetermined address component,  
6                   then accessing a memory location at the first address,  
7                   the first address comprising a plurality of address bits, wherein the  
8                   predetermined address component comprises less than all of the address bits of the first  
9                   address,  
10                  the first address and the second address having a common address component.

1                   2.       The method of claim 1 wherein the predetermined address component  
2                   comprises the high order byte of the first address.

1                   3.       The method of claim 1 further comprising executing a virtual machine  
2                   in a first page of an address space of the data processing unit, the first address being an  
3                   address in the first page, wherein the second address is an address in another page of the  
4                   address space of the data processing unit.

1                   4        The method of claim 1 wherein an address space of the data processing  
2                   unit comprises a plurality of pages, the first address being an address in a first page, the  
3                   second address being in an address in a second page that is different from the first page.

1                   5.       A data processor comprising a memory management unit for handling  
2                   addresses, the memory management unit comprising:

3                   address input lines for presenting an input address;

4                   address translation logic coupled to at least some of the address input lines;

5                   and

6                   address output lines coupled to the address translation logic for presenting an  
7                   output address,

8                   the address translation logic operable to receive a first input address from the  
9                   address input lines and to generate a first output address on the address output lines that is  
10                  different from the first input address if a portion of the first input address contains a  
11                  predetermined value.

1                   6.       The data processor of claim 5 wherein the address translation logic is  
2 further configured to detect a predetermined value present in the high order bits of the input  
3 address.

1                   7.       The data processor of claim 5 wherein the memory management unit  
2 further comprises a translation table, the translation table comprising M-bit values, the  
3 translation table addressed by an N-bit value, where  $M > N$ , wherein the translation table  
4 produces one of the M-bit values based on N lines of the address input lines, wherein the M-  
5 bit value produced is used in M lines of the address output lines.

1                   8.       The data processor of claim 7 wherein the remaining lines in the  
2 address output lines come from the address input lines.

1                   9.       A method for transferring data in a data processing unit comprising:  
2                   accessing a first value from a first data storage component of the data  
3 processing unit;  
4                   combining the first value with a base address to produce a first address, the  
5 base address representative of an area in a memory;  
6                   accessing a second value from a second data storage component of the data  
7 processing unit;  
8                   accessing a third value from a third data storage component of the data  
9 processing unit;  
10                  combining the second value with a value stored in a location in the memory  
11 indicated by the first address to produce a fourth value;  
12                  comparing the third value with the fourth value to produce a comparison  
13 result; and  
14                  based on the comparison result, either accessing the memory beginning at a  
15 location indicated by a second address or performing an exception operation, the second  
16 address being computed from the base address.

1                   10.      The method of claim 9 further including one or more steps of storing  
2 the first value in the first data storage component, storing the second value in the second data  
3 storage component, and storing the third value, wherein the one or more steps of storing are  
4 performed only at the time the data processing unit is initialized.

1                    11.    The method of claim 9 wherein one or more of the first value, the  
2    second value, and third value is stored respectively in the first data storage component, the  
3    second data storage component, and the third data storage component in a non-volatile  
4    manner.

1                    12.    The method of claim 9 further comprising loading one or more of the  
2    first data storage component, the second data storage component, and the third data storage  
3    component respectively with the first value, the second value, and third value.

1                    13.    The method of claim 9 wherein the second address is computed based  
2    on the base address and an offset value.

1                    14.    The method of claim 13 wherein the second address is computed by  
2    adding together the base address and the offset value.

1                    15.    The method of claim 9 wherein the exception operation comprises  
2    accessing content of a fourth data storage component, wherein subsequent processing by the  
3    data processing unit continues from instructions beginning at a location in memory computed  
4    based on the content of the fourth data storage component.

1                    16.    The method of claim 15 wherein the location in memory where  
2    subsequent processing continues is computed by adding the content of the fourth data storage  
3    component with an offset value.

1                    17.    The method of claim 9 wherein the area in memory represents a data  
2    object.

1                    18.    The method of claim 9 wherein the step of accessing is a step of  
2    copying the accessed content to another area in the memory.

1                    19.    The method of claim 9 wherein the step of accessing is a step of  
2    writing information to the accessed content.

1                    20.    The method of claim 9 wherein the first address is produced by adding  
2    together the first value and the base address.

1                    21.    A data processing unit comprising:

2 a memory;  
 3 instruction decoder logic for producing control signals in response to decoding  
 4 program instructions;  
 5 data processing logic coupled to receive the control signals and configured to  
 6 perform logic operations in accordance with the control signals;  
 7 an instruction register coupled to the memory and to the instruction decoder,  
 8 the instruction register operable to store an instruction to be decoded;  
 9 a program counter operable to store an address of an instruction to be decoded;  
 10 a vector address data area for storing a vector address;  
 11 a first data area for storing a first value;  
 12 a second data area for storing a second value; and  
 13 a third data area for storing a third value,  
 14 the instruction decoder configured to assert first control signals in response to  
 15 decoding a first instruction,  
 16 the data processing logic, in response to the first control signals, configured to:  
 17 combine the first value with a first operand contained in the first instruction to  
 18 produce a first address;  
 19 combine the second value with a value stored in the memory at a location  
 20 indicated by the first address to produce a fourth value;  
 21 compare the third value with the fourth value to produce a comparison result;  
 22 and  
 23 based on the comparison result, either access the memory beginning at a  
 24 location indicated by a second address or update the program counter with an address based  
 25 on the vector address, the second address being computed from the first operand.

1 22. The data processing unit of claim 21 wherein the memory is a re-  
 2 programmable, non-volatile memory.

1 23. The data processing unit of claim 21 wherein the memory is one of an  
 2 EEPROM (electrically erasable programmable read-only memory) and flash memory.

1 24. The data processing unit of claim 21 wherein the data processing logic,  
 2 in response to initialization of the data processing unit, is further configured to load data into  
 3 one or more of the vector address data area, the first data area, the second data area, and the  
 4 third data area.

1                   25.     The data processing unit of claim 21 wherein one or more of the vector  
2 address data area, the first data area, the second data area, and the third data area comprise  
3 non-volatile memory.

1                   26.     The data processing unit of claim 25 wherein the non-volatile memory  
2 is one of EEPROM (electrically erasable programmable read-only memory) or PROM  
3 (programmable read-only memory).

1                   27.     The data processing unit of claim 21 wherein one or more of the vector  
2 address data area, the first data area, the second data area, and the third data area comprise  
3 hard-wired logic.

1                   28.     The data processing unit of claim 21 wherein the instruction decoder is  
2 further configured to assert a second set of control signals in response to decoding a second  
3 instruction, the data processing logic, in response to the second control signals, is further  
4 configured to load data into one or more of the vector address data area, the first data area,  
5 the second data area, and the third data area, the data contained in the second instruction.

1                   29.     The data processing unit of claim 21 wherein the data processing logic,  
2 in response to the first control signals, is further configured to combine the first operand with  
3 a second operand contained in the first instruction to produce the second address.

1                   30.     The data processing unit of claim 29 wherein the first operand and the  
2 second operand are summed to produce the second address.

1                   31.     A memory access method in a data processing unit comprising re-  
2 programmable non-volatile memory, the method comprising:

3                   detecting a write operation to an area in the re-programmable non-volatile  
4 memory;

5                   determining a caching location which identifies an area of memory in a  
6 dynamic memory to which data to be written by the write operation can be cached, the area of  
7 memory identified by the caching location referred to as a caching area; and

8                   writing the data to the caching area instead of writing the data to the area in  
9 the re-programmable non-volatile memory,

10                    wherein the caching area is associated with the area in the re-programmable  
11 non-volatile memory.

1                    32.     The method of claim 31 wherein the step of determining a caching  
2 location comprises:  
3                    determining if the data can be stored in the dynamic memory, and if not then:  
4                    identifying one or more memory locations in the dynamic memory;  
5                    and  
6                    writing content in the one or more memory locations to the re-  
7 programmable non-volatile memory; and  
8                    providing an address in the dynamic memory as the caching location in the  
9 area of memory.

1                    33.     The method of claim 32 wherein the step of determining a caching  
2 location in the dynamic memory is limited to determining a caching location in a segment of  
3 the dynamic memory.

1                    34.     The method of claim 31 further including detecting a second write  
2 operation to the area in the re-programmable non-volatile memory and writing the data  
3 associated with the second write operation to the area of memory identified by the caching  
4 location instead of writing the data to the area in the re-programmable non-volatile memory.

1                    35.     The method of claim 31 further including detecting a second write  
2 operation to a second area in the re-programmable non-volatile memory, determining if there  
3 is a caching area in the dynamic memory that is associated with the second area and if there is  
4 then writing data associated with the second write operation to the caching area associated  
5 with the second area.

1                    36.     The method of claim 31 wherein an address space of the re-  
2 programmable non-volatile memory is equal to or greater than an address space of the  
3 dynamic memory.

1                    37.     The method of claim 32 wherein the step of identifying one or more  
2 memory locations is based on the size of the data.

1                   38.     The method of claim 32 wherein the step of identifying one or more  
2 memory locations is based on contents of the data.

1                   39.     The method of claim 38 wherein the step of identifying one or more  
2 memory locations includes applying a hash function on the data to produce a hash result, the  
3 one or more locations determined based on the hash result.

1                   40.     The method of claim 31 wherein the re-programmable non-volatile  
2 memory is one of an EEPROM (electrically erasable programmable read-only memory) and a  
3 flash memory.

1                   41.     The method of claim 31 further including obtaining an address range  
2 which defines the area of memory in the dynamic memory.

1                   42.     The method of claim 31 further including detecting a read operation  
2 from the re-programmable non-volatile memory and reading the re-programmable non-  
3 volatile memory to effect the read operation.

1                   43.     The method of claim 31 further including detecting a read operation  
2 from the re-programmable non-volatile memory and reading one or more memory locations  
3 from the area of memory in the dynamic memory to effect the read operation.

1                   44.     A data processing unit comprising:  
2                   a bus for accessing a dynamic memory;  
3                   a re-programmable non-volatile memory;  
4                   memory access logic operatively coupled to the memory bus and to the re-  
5 programmable non-volatile memory; and  
6                   processor logic operatively coupled to the memory access logic to transfer  
7 data with the dynamic memory via the memory bus and to transfer data with the re-  
8 programmable non-volatile memory,  
9                   the memory access logic configured to detect a write operation to the re-  
10 programmable non-volatile memory,  
11                  the processor logic configured to respond to the memory access logic  
12 detecting the write operation and to:

13                    identify a caching location in the area of memory wherein data to be  
14                    written by the write operation can be cached; and  
15                    store the data in the area of memory identified by the caching location.

1                    45.     The data processing unit of claim 44 wherein the memory access logic  
2                    is further configured to:  
3                    determine if the data can be stored in the area of memory; and  
4                    provide an address in the area of memory as the caching location in the area of  
5                    memory,  
6                    wherein if it is determined that the data cannot be stored in the area of  
7                    memory, then:  
8                    identify one or more memory locations in the area of memory; and  
9                    write content in the one or more memory locations to the re-programmable  
10                   non-volatile memory,  
11                   wherein the one or more memory locations are available for caching a write  
12                   operation.

1                    46.     The data processing unit of claim 44 wherein an address space of the  
2                    re-programmable non-volatile memory is equal to or greater than an address space of the  
3                    dynamic memory.

1                    47.     The data processing unit of claim 44 wherein the re-programmable  
2                    non-volatile memory is one of an EEPROM (electrically erasable programmable read-only  
3                    memory) and a flash memory.

1                    48.     The data processing unit of claim 44 wherein the dynamic memory is a  
2                    random access memory.

1                    49.     The data processing unit of claim 44 wherein the memory access logic  
2                    is further configured to detect a read operation from the re-programmable non-volatile  
3                    memory and to effect a read operation therefrom.

1                    50.     The data processing unit of claim 44 wherein the memory access logic  
2                    is further configured to detect a read operation from the re-programmable non-volatile  
3                    memory and to access the area in memory in the dynamic memory to effect the read  
4                    operation.



1           51.     A memory access method comprising:  
2           detecting a write operation to a re-programmable non-volatile memory; and  
3           if a destination address associated with the write operation is within a first  
4 range of addresses, then performing a fast write operation of data associated with the write  
5 operation to the re-programmable non-volatile memory.

1           52.     The method of claim 51 wherein the first range of addresses spans the  
2 entire address space of the re-programmable non-volatile memory.

1           53.     The method of claim 51 wherein if the destination address is not within  
2 the first range of addresses, then performing a slow write operation of the data to the re-  
3 programmable non-volatile memory.

1           54.     The method of claim 51 wherein the first range of addresses spans a  
2 range of addresses less than the address space of the re-programmable non-volatile memory.

1           55.     The method of claim 51 wherein the step of performing a fast write  
2 operation is performed if the destination address falls within any of a plurality of ranges of  
3 addresses.

1           56.     A memory access method comprising:  
2           detecting a write operation to a non-volatile memory;  
3           determining an access mode;  
4           if the access mode is a first mode, then performing a fast write operation of  
5 data associated with the write operation to the non-volatile memory;  
6           if the access mode is a second mode, then performing a slow write operation  
7 of the data associated with the write operation; and  
8           if the access mode is a third mode, then:  
9                 if the destination address associated with the write operation is within a  
10 first range of addresses, then performing a fast write operation of the data associated  
11 with the write operation to the non-volatile memory;  
12                 if the destination address is not within the first range of addresses, then  
13 performing a slow write operation of the data to the non-volatile memory; and  
14           if the access mode is a fourth mode, then:

15                   determining a caching location which identifies an area of memory in a  
16           dynamic memory to which data to be written by the write operation can be cached, the  
17           area of memory identified by the caching location referred to as a caching area; and  
18                   writing the data to the caching area instead of writing the data to the  
19           area in the non-volatile memory,  
20                   wherein the caching area is associated with the area in the non-volatile  
21   memory.

1                   57.    A memory control logic for accessing a re-programmable non-volatile  
2   memory comprising:

3                   write detection logic to determine when a write operation to the memory is  
4   being performed;

5                   address detection logic configured to indicate a detected address when a  
6   destination address associated with a write operation falls within a first range of addresses;  
7   and

8                   write-control logic operatively coupled to the address detection logic and  
9   configured to perform a shallow-write operation of data associated with the write operation  
10   when the address detection logic indicates a detected address.

1                   58.    The memory control logic of claim 57 further comprising a first  
2   address register and a second address register, wherein the first range of addresses comprises  
3   data stored in the first and second address registers.

1                   59.    The memory control logic of claim 57 further comprising a plurality of  
2   register pairs, each register pair representative of a range of addresses in an address space of  
3   the memory, wherein the address detection logic is further configured to indicate a detected  
4   address when the destination address falls within any of the ranges of addresses represented  
5   by the plurality of register pairs.

1                   60.    The memory control logic of claim 57 wherein the re-programmable  
2   non-volatile memory is one of an EEPROM (electrically erasable programmable read-only  
3   memory) and a flash memory.

1                   61.    A memory control logic for accessing a re-programmable non-volatile  
2   memory comprising write detection logic to determine when a write operation to the memory

3 is being performed and write-control logic configured to perform a shallow-write operation of  
4 data associated with the write operation.

1                   62.     The memory control logic of claim 61 wherein the re-programmable  
2 non-volatile memory is one of an EEPROM (electrically erasable programmable read-only  
3 memory) and a flash memory.

1                   63.     A memory access method for accessing a re-programmable non-  
2 volatile memory comprising:

3                   detecting a write operation to the re-programmable non-volatile memory, the  
4 write operation having an associated destination address and associated one or more data to  
5 be written to the re-programmable non-volatile memory;

6                   determining an operating mode;

7                   if the operating mode indicates a first mode of operation, then:

8                   performing a partial write operation of each datum to the re-  
9 programmable non-volatile memory, if the destination address is within a first range  
10 of addresses; and

11                   performing a full write operation of each datum to the re-  
12 programmable non-volatile memory, otherwise;

13                   if the operating mode indicates a second mode of operation, then performing a  
14 full write operation of each datum to the re-programmable non-volatile memory;

15                   if the operating mode indicates a third mode of operation, then performing a  
16 partial write operation of each datum to the re-programmable non-volatile memory; and

17                   if the operating mode indicates a fourth mode of operation, then:

18                   determining a caching location which identifies an area of memory in a  
19 dynamic memory where the data can be cached; and

20                   writing the data in the area of memory identified by the caching  
21 location instead of writing to the re-programmable non-volatile memory.

1                   64.     The method of claim 63 wherein the re-programmable non-volatile  
2 memory is one of an EEPROM (electrically erasable programmable read-only memory) and a  
3 flash memory.